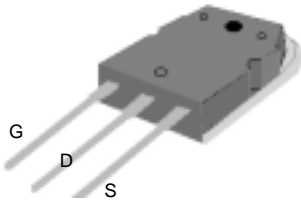


N-channel Enhancement-mode Power MOSFET

PRODUCT SUMMARY

BV_{DSS}	900V
$R_{DS(ON)}$	1.2 Ω
I_D	8.6A

 **Pb-free; RoHS-compliant TO-247**



TO-247 (suffix W)

DESCRIPTION

The SSM09N90GW achieves fast switching performance with low gate charge without a complex drive circuit. It is suitable for high voltage applications such as AC/DC converters and offline power supplies.

The SSM09N90GW is in a TO-247 (TO-3P) package, which is widely used for commercial and industrial applications, where the greater pin spacing is needed to meet safety specifications. The through-hole package is suitable for vertical mounting, where a small footprint is required on the board, and/or an external heatsink is to be attached.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Units
V_{DS}	Drain-source voltage	900	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Continuous drain current, $T_C = 25^\circ\text{C}$	8.6	A
	$T_C = 100^\circ\text{C}$	5	A
I_{DM}	Pulsed drain current ¹	30	A
P_D	Total power dissipation, $T_C = 25^\circ\text{C}$	240	W
	Linear derating factor	1.92	W/ $^\circ\text{C}$
E_{AS}	Single pulse avalanche energy ³	92	mJ
I_{AS}	Avalanche current	5.2	A
E_{AR}	Repetitive avalanche energy	8.6	mJ
T_{STG}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Maximum thermal resistance, junction-case	0.52	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum thermal resistance, junction-ambient	40	$^\circ\text{C}/\text{W}$

Notes:

1. Pulse width must be limited to avoid exceeding the safe operating area.
2. Pulse width <300us, duty cycle <2%.
3. Starting $T_j=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $L=6.8\text{mH}$, $R_G=25\Omega$, $I_{AS}=5.2\text{A}$.

ELECTRICAL CHARACTERISTICS (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-source breakdown voltage	$V_{GS}=0V, I_D=1mA$	900	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown voltage temperature coefficient	Reference to $25^\circ\text{C}, I_D=1mA$	-	0.67	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static drain-source on-resistance	$V_{GS}=10V, I_D=4.5A$	-	-	1.2	Ω
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward transconductance	$V_{DS}=10V, I_D=4.5A$	-	11.5	-	S
I_{DSS}	Drain-source leakage current	$V_{DS}=900V, V_{GS}=0V$ $V_{DS}=720V, V_{GS}=0V, T_j = 125^\circ\text{C}$	-	-	10 100	μA μA
I_{GSS}	Gate-source leakage current	$V_{GS}=\pm 30V$	-	-	± 100	nA
Q_g	Total gate charge ²	$I_D=8.6A$	-	67.1	120	nC
Q_{gs}	Gate-source charge	$V_{DS}=540V$	-	17	-	nC
Q_{gd}	Gate-drain ("Miller") charge	$V_{GS}=10V$	-	19.9	-	nC
$t_{d(on)}$	Turn-on delay time ²	$V_{DS}=450V$	-	25.8	-	ns
t_r	Rise time	$I_D=5A$	-	10.3	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G=10\Omega, V_{GS}=10V$	-	305	-	ns
t_f	Fall time	$R_D=90\Omega$	-	536	-	ns
C_{iss}	Input capacitance	$V_{GS}=0V$	-	4087	6000	pF
C_{oss}	Output capacitance	$V_{DS}=25V$	-	221	-	pF
C_{rss}	Reverse transfer capacitance	$f=1.0MHz$	-	51	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward voltage ²	$I_S=8.6A, V_{GS}=0V$	-	-	1.5	V
I_S	Continuous source current (body diode)	$V_D=V_G=0V, V_S=1.5V$	-	-	8.6	A
I_{SM}	Pulsed source current (body diode) ¹		-	-	3	A

Notes:

1.Pulse width must be limited to avoid exceeding the maximum junction temperature of 150°C .

2.Pulse width $<300\mu s$, duty cycle $<2\%$.

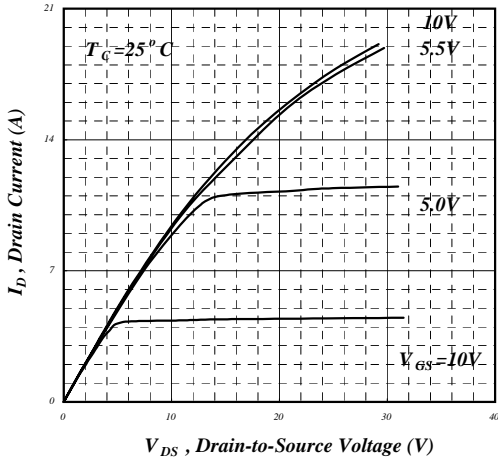


Fig 1. Typical Output Characteristics

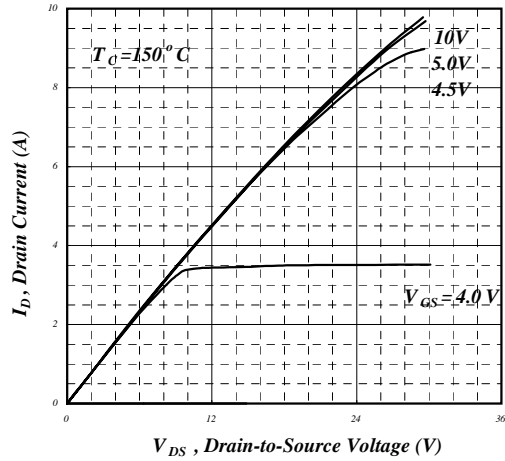


Fig 2. Typical Output Characteristics

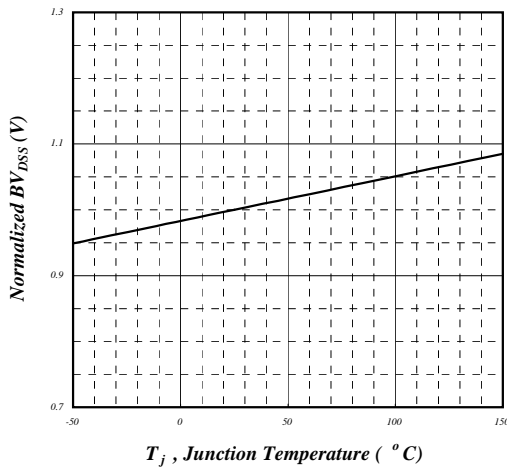


Fig 3. Normalized BVD_{SS} vs. Junction Temperature

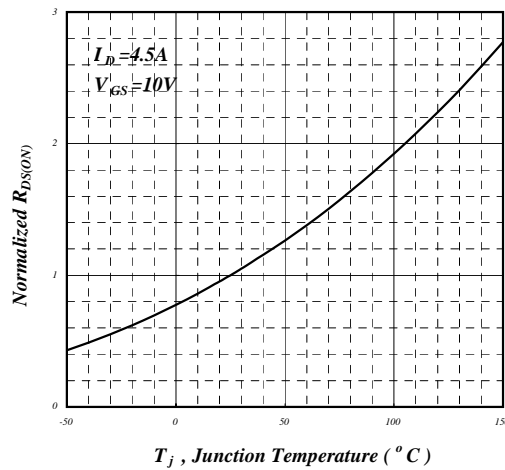


Fig 4. Normalized On-Resistance vs. Junction Temperature

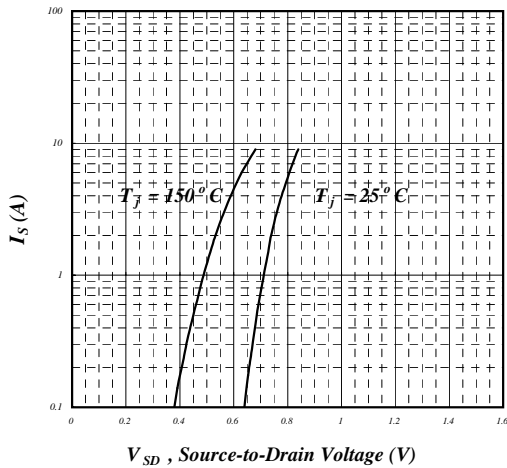


Fig 5. Forward Characteristic of Reverse Diode

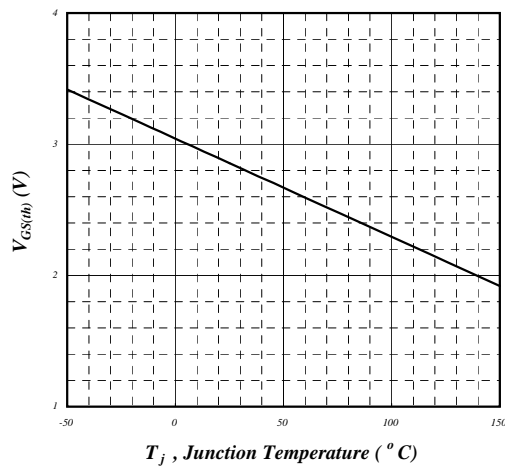


Fig 6. Gate Threshold Voltage vs. Junction Temperature

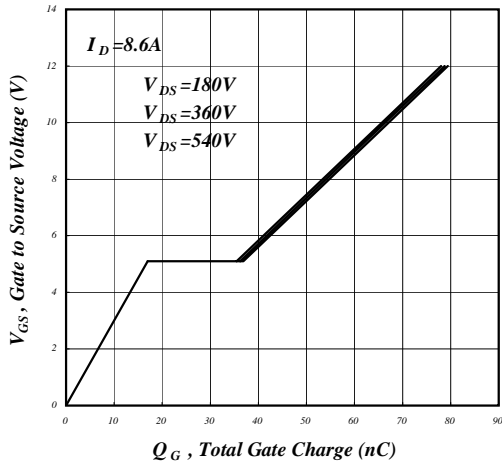


Fig 7. Gate Charge Characteristics

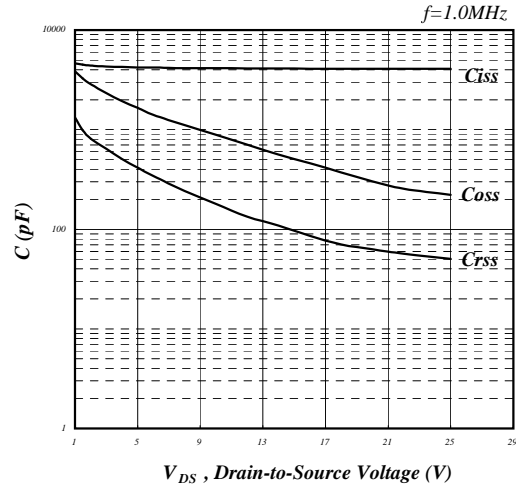


Fig 8. Typical Capacitance Characteristics

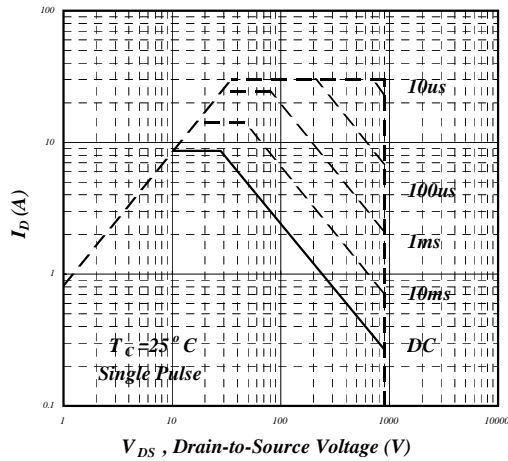


Fig 9. Maximum Safe Operating Area

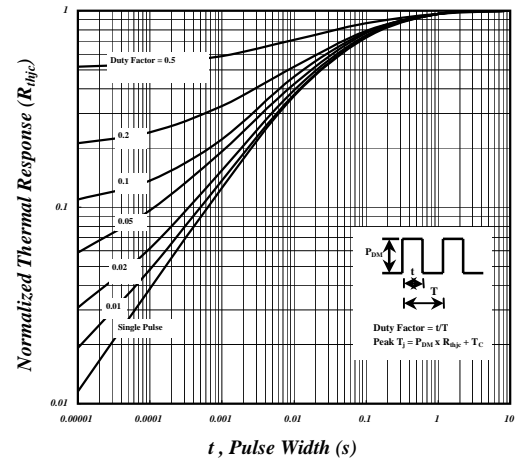


Fig 10. Effective Transient Thermal Impedance

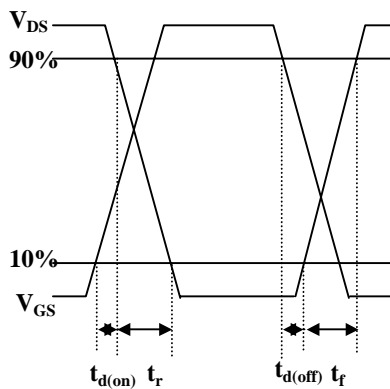


Fig 11. Switching Time Waveform

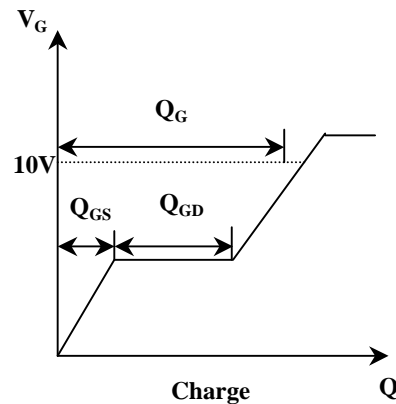
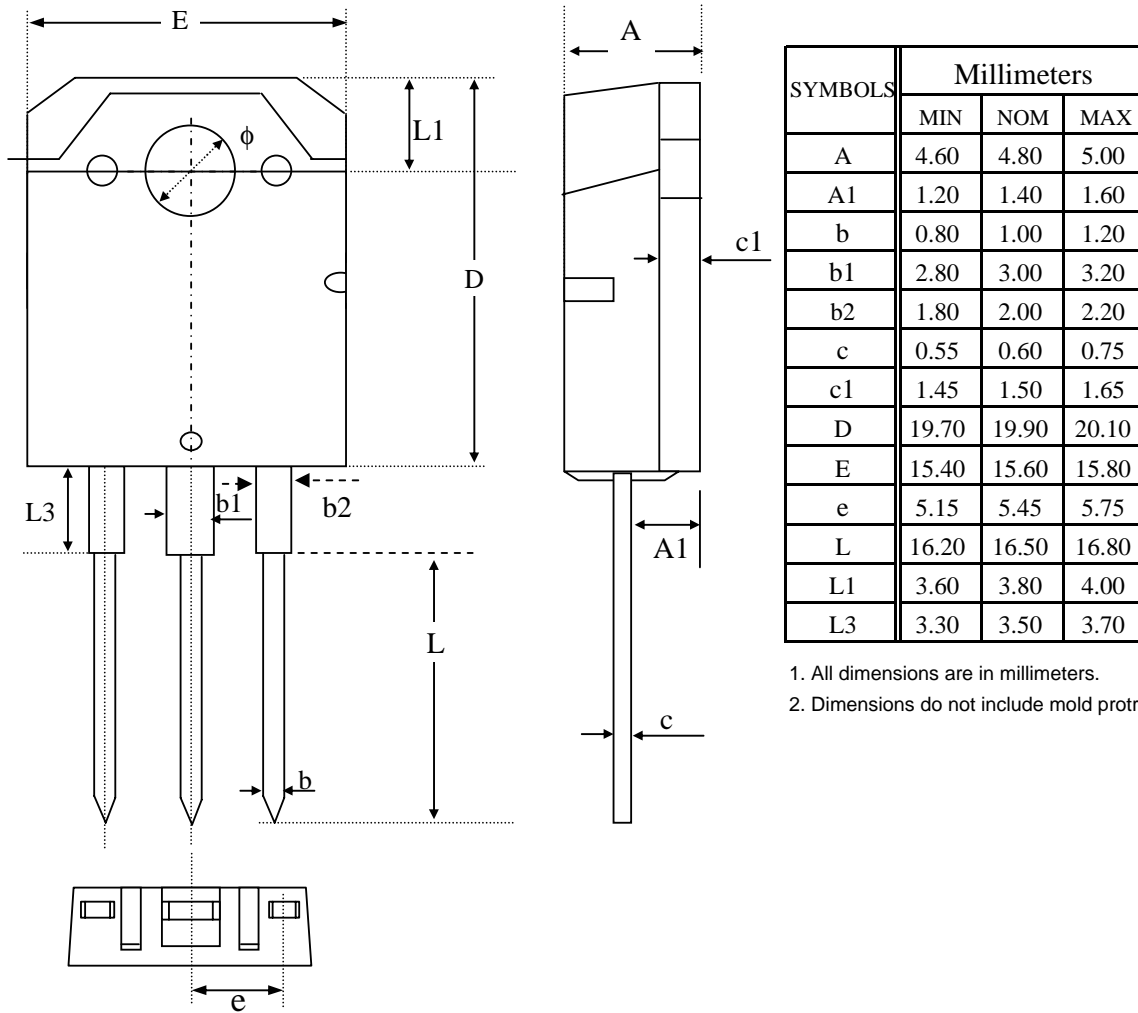


Fig 12. Gate Charge Waveform

PHYSICAL DIMENSIONS - TO-247

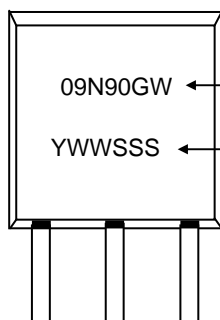


1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

PART MARKING - TO-247

PACKING: Moisture sensitivity level MSL3

1000pcs in tubes packed inside a moisture barrier bag (MBB).



PART NUMBER: 09N90GW = SSM09N90GW

DATE/LOT CODE:

Y = last digit of the year
 WW = work week (01 -> 52)
 SSS = lot code sequence

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